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DDR3

DDR2

DDR

SDR

Speciality

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Modems

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DRAM DDR3

RDIMM

RDIMM

UDIMM

SODIMM

mini DIMM


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DDR3 is the current mainstream dram technology standardized by JEDEC, bringing further improvements in power consumption and increased bandwidth over DDR2. Available in power supply voltages of 1.5V (DDR3) and 1.35V (DDR3L) and with transfer data rates from 800Mb/s to 1.6Gb/s and beyond, DDR3 has become the de facto mainstream memory technology especially for server and notebook applications in the 1H of 2010. Many other applications are available in the market today to take advantage of the superior performance features of DDR3 and DDR3L. Wintec currently offers following DDR3 and DDR3L Modules and will continue to add more solutions as DDR3/DDR3L enabled applications will proliferate.

DDR3 240-Pin Registered-ECC DIMMs

Standard Profile (1.181") with Nominal Voltage (1.5V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD3RE01GX809-xxxxx-yyz	1 rank	128x72	128Mx8	1.5V
2GB	WD3RE02GX818-xxxxx-yyz	2 rank	256x72	128Mx8	1.5V
	WD3RE02GX809-xxxxx-yyz	1 rank	256x72	256Mx8	1.5V
	WD3RE02GX418-xxxxx-yyz	1 rank	256x72	256Mx4	1.5V
4GB	WD3RE04GX418-xxxxx-yyz	1 rank	512x72	512Mx4	1.5V
	WD3RE04GX818-xxxxx-yyz	2 rank	512x72	256Mx8	1.5V
	WD3RE04GX436-xxxxx-yyz	2 rank	512x72	256Mx4	1.5V
8GB	WD3RE08GX436-xxxxx-yyz	2 rank	1024x72	512Mx4	1.5V
	WD3RE08GX836-xxxxx-yyz	4 rank	1024x72	256Mx8	1.5V

	WD3RE08GX418-xxxxx-yyz	1 rank	1024x72	1024Mx4	1.5V
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Very Low Profile (0.72") with Nominal Voltage (1.5V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD3RE01GX809V-xxxxx-yyz	1 rank	128x72	128Mx8	1.5V
2GB	WD3RE02GX818V-xxxxx-yyz	2 rank	256x72	128Mx8	1.5V
	WD3RE02GX809V-xxxxx-yyz	1 rank	256x72	256Mx8	1.5V
	WD3RE02GX418V-xxxxx-yyz	1 rank	256x72	256Mx4	1.5V
4GB	WD3RE04GX418V-xxxxx-yyz	1 rank	512x72	512Mx4	1.5V
	WD3RE04GX818V-xxxxx-yyz	2 rank	512x72	256Mx8	1.5V
8GB	WD3RE08GX418V-xxxxx-yyz	1 rank	1024x72	1024Mx4	1.5V

Standard Profile (1.181") with Low Voltage (1.35V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD3LE01GX809-xxxxx-yyz	1 rank	128x72	128Mx8	1.35V
2GB	WD3LE02GX818-xxxxx-yyz	2 rank	256x72	128Mx8	1.35V
	WD3LE02GX809-xxxxx-yyz	1 rank	256x72	256Mx8	1.35V
	WD3LE02GX418-xxxxx-yyz	1 rank	256x72	256Mx4	1.35V
4GB	WD3LE04GX418-xxxxx-yyz	1 rank	512x72	512Mx4	1.35V
	WD3LE04GX818-xxxxx-yyz	2 rank	512x72	256Mx4	1.35V
	WD3LE04GX436-xxxxx-yyz	2 rank	512x72	256Mx4	1.35V
8GB	WD3LE08GX436-xxxxx-yyz	2 rank	1024x72	512Mx4	1.35V
	WD3LE08GX836-xxxxx-yyz	4 rank	1024x72	256Mx8	1.35V
	WD3LE08GX418-xxxxx-yyz	1 rank	1024x72	1024Mx4	1.35V

Very Low Profile (0.72") with Low Voltage (1.35V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD3LE01GX809V-xxxxx-yyz	1 rank	128x72	128Mx8	1.35V
2GB	WD3LE02GX818V-xxxxx-yyz	2 rank	256x72	128Mx8	1.35V
	WD3LE02GX809V-xxxxx-yyz	1 rank	256x72	256Mx8	1.35V
	WD3LE02GX418V-xxxxx-yyz	1 rank	256x72	256Mx4	1.35V
4GB	WD3LE04GX418V-xxxxx-yyz	1 rank	512x72	512Mx4	1.35V
	WD3LE04GX418V-xxxxx-yyz	2 rank	512x72	256Mx4	1.35V
8GB	WD3LE08GX418V-xxxxx-yyz	1 rank	1024x72	1024Mx4	1.35V

(xxxx) Module speed (MHz) and Cas Latency

= 1066J : 1066MHz CL 7
1333L : 1333MHz CL9
1600N :1600MHz CL11

DRAM Manufacturer and Die Revision

(yy) = P: Samsung A: A-Die
H: Micron B: B-Die
C: Hynix C: C-Die

Buffer / Register set (Only applies to Registered/Buffered modules)

(z) = I: Inphi
D: IDT
L: Intel